

# **PMT200EPEX Datasheet**

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DiGi Electronics Part Number PMT200EPEX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMT200EPEX

Description MOSFET P-CH 70V 2.4A SOT223

Detailed Description P-Channel 70 V 2.4A (Ta) 800mW (Ta) Surface Mou

nt SOT-223



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PMT200EPEX	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
70 V	2.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
4.5V, 10V	167mOhm @ 2.4A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250μA	15.9 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	822 pF @ 35 V
FET Feature:	Power Dissipation (Max):
	800mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-223	TO-261-4, TO-261AA
Base Product Number:	
PMT200	

# **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

Product data sheet

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-70	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	[1]	-	-	-2.4	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C		-	130	167	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain	G G G G G G G G G G G G G G G G G G G	
3	S	source		G $\downarrow$ $\downarrow$ $\downarrow$ $\downarrow$
4	D	drain		S 017aaa259

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PMT200EPE	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PMT200EPE	T2EPE

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-70	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.4	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-9.7	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	800	mW
			[1]	-	1.75	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -1.3 A; DUT in avalanche (unclamped)		-	19.5	mJ
Source-drain d	liode					,
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.8	Α
ESD maximum	rating		'	,		
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Measured between all pins.

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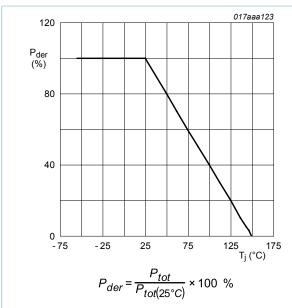


Fig. 1. Normalized total power dissipation as a function of junction temperature

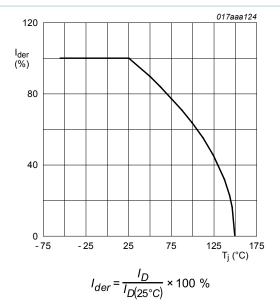


Fig. 2. Normalized continuous drain current as a function of junction temperature

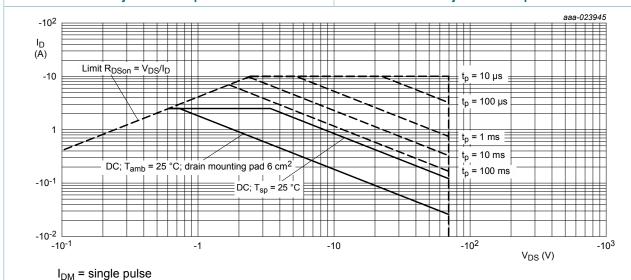


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-

source voltage

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#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance	in free air	[1]	-	135	155	K/W
	from junction to ambient		[2]	_	54	70	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	7	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

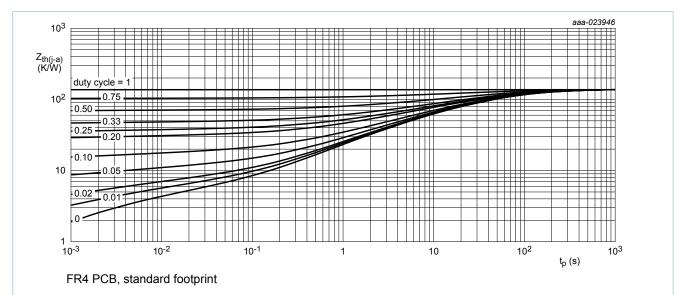


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

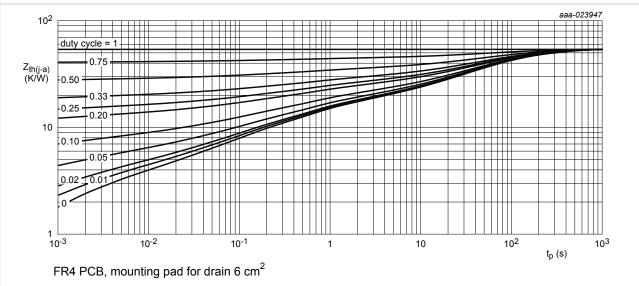


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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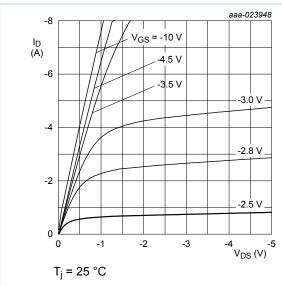
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### 10. Characteristics

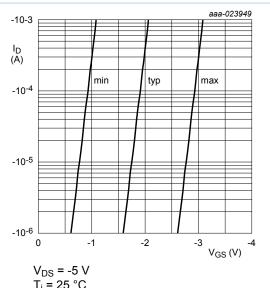
#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-70	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-1	-2	-3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -70 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub> gate	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub> drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	130	167	mΩ	
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.4 A; T <sub>j</sub> = 150 °C	-	234	250	mΩ
		$V_{GS}$ = -4.5 V; $I_D$ = -2.1 A; $T_j$ = 25 °C	-	150	225	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	13.5	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	12	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -35 V; $I_{D}$ = -2.4 A; $V_{GS}$ = -10 V;	-	10.6	15.9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.2	-	nC
$Q_{GD}$	gate-drain charge		-	1.05	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -35 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	822	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	47	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	31.5	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -35 \text{ V}; I_D = -2.4 \text{ A}; V_{GS} = -10 \text{ V};$	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	42	-	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-dra	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -2.4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.8	-1.2	V

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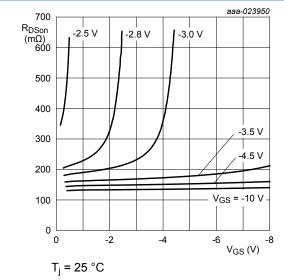


Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values

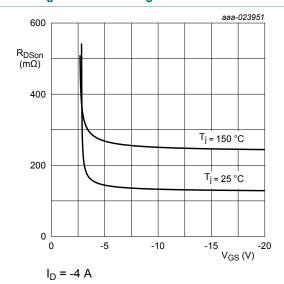


T<sub>i</sub> = 25 °C

Sub-threshold drain current as a function of Fig. 7. gate-source voltage



Drain-source on-state resistance as a function Fig. 8. of drain current; typical values



Drain-source on-state resistance as a function Fig. 9. of gate-source voltage; typical values

#### 70 V, P-channel Trench MOSFET

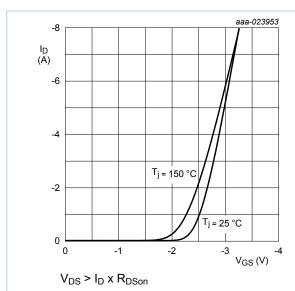


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

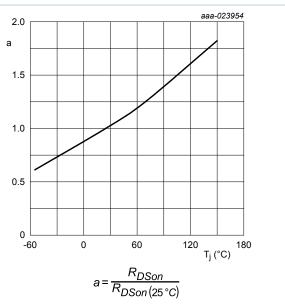


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

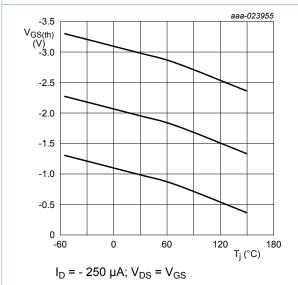


Fig. 12. Gate-source threshold voltage as a function of junction temperature

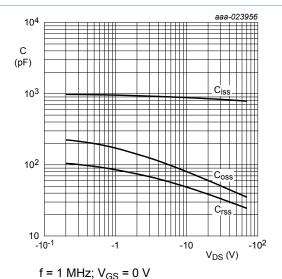
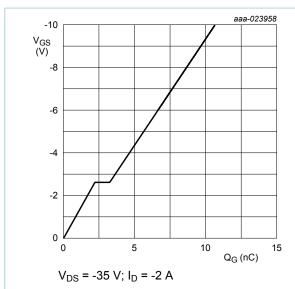


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)
V<sub>GS(th)</sub>
V<sub>GS</sub>
Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>GGtot)</sub>
003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

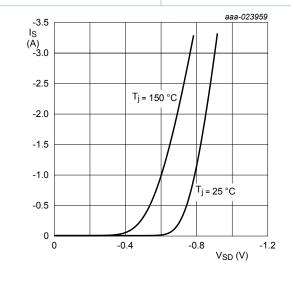
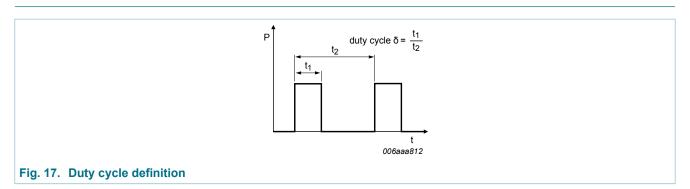


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

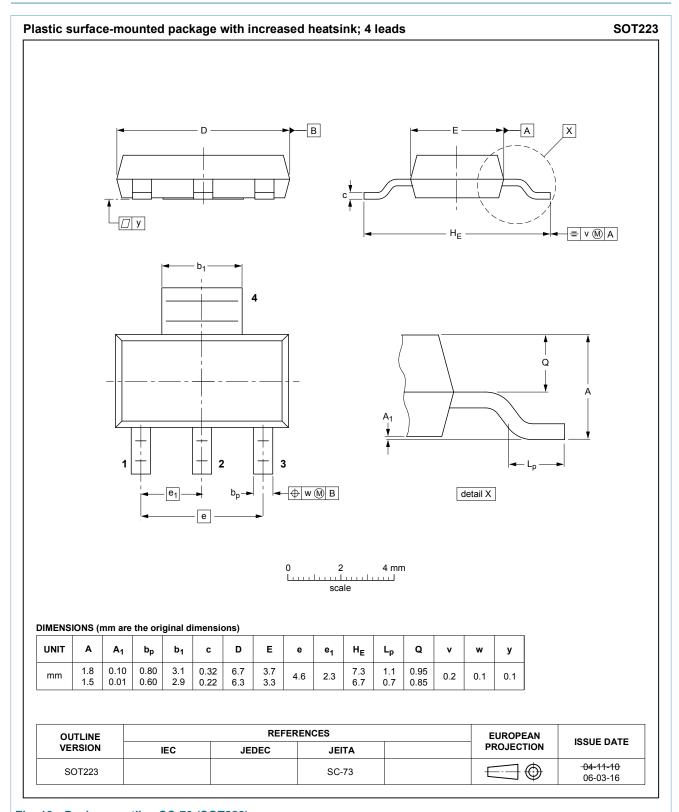
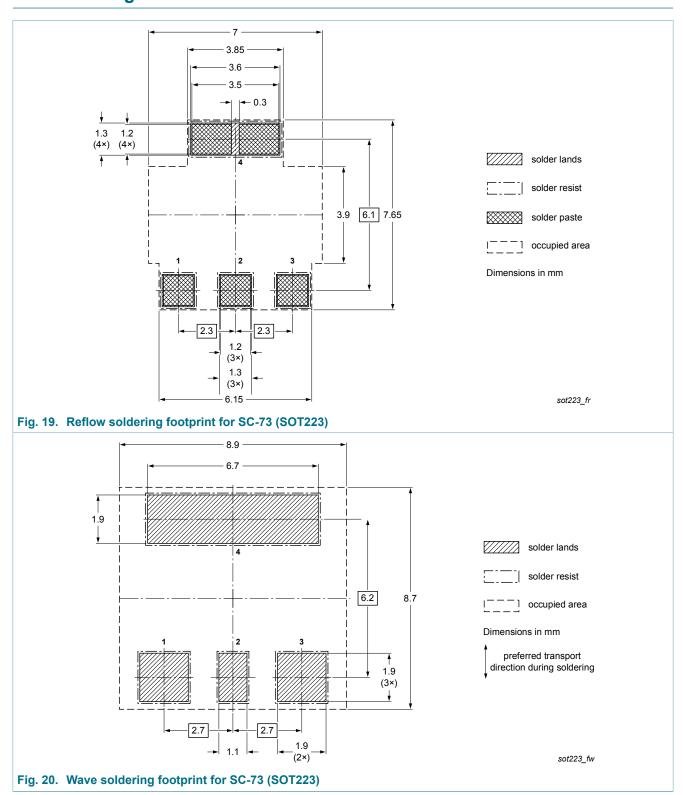


Fig. 18. Package outline SC-73 (SOT223)

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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMT200EPE v.1	20180314	Product data sheet	-	-

#### 70 V, P-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PMT200EPE

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